

http://www.kttic.commitsubishi semiconductor (GaAs FET)

MGFX39V0717

10.7~11.7GHz BAND 8W INTERNALLY MATCHD GaAs FET

DESCRIPTION

The MGFX39V0717 is an internally impedance matched GaAs power FET especially designed for use in $10.7 \sim 11.7$ GHz band amplifiers. The hermetically sealed metal-ceramic package guarantees high reliability.

FEATURES

- Internally impedance matched
- High output power

 $P_{1dB} = 8 W (TYP.) @ f = 10.7 \sim 11.7 GHz$

• High linear power gain

G_{LP} = 7.0 dB (TYP.) @ f = 10.7~11.7 GHz

High power added efficiency

 $\eta_{\text{add}} = 26\% \text{ (TYP.)} @ f = 10.7 \sim 11.7 \text{ GHz}, P_{1dB}$

APPLICATION

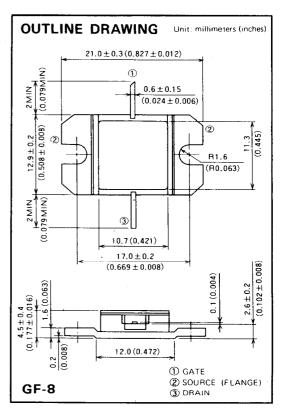
For use in 10.7~11.7 GHz band amplifiers

QUALITY GRADE

• IG

RECOMMENDED BIAS CONDITIONS

- V_{DS}=10V
- I_D=2.4A
- Refer to Bias Procedure



TINGS (To = 25°C)

ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

Symbol	Parameter		Rating	Unit
V _{GDO}	Gate to drain voltage		-15	V
V _{GSO}	Gate to source voltage		-15	V
ID	Drain current		5.6	А
I _{GR}	Reverse gate current		-18	mA
I _{GF}	Forward gate current		36	mA
PT	Total power dissipation	*1	42.8	w
Tch	Channel temperature		175	.c
Tstg	Storage temperature		-65~+175	°C

^{*1:} Tc=25°C

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

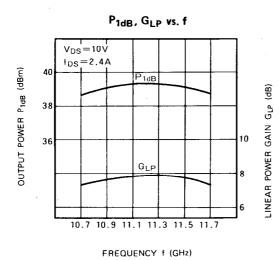
Symbol	Parameter	Tank and distance		Limits		
		Test conditions	Min	Тур	Min	Unit
loss	Saturated drain current	$V_{DS}=3V$, $V_{DS}=0V$		4.0	5.6	А
g _m	Transconductance	V _{DS} =3V, I _D =2.2A —		2.0	_	S
Vgs(off)	Gate to source cut-off voltage	$V_{DS} = 3V$, $I_D = 20 \text{mA}$	- 2	-3	-4	V
P _{1dB}	Output power at 1dB gain compression		37.5	39		dBm
G_{LP}	Linear power gain	$V_{DS} = 10V$, $I_D = 2.4A$, $f = 10.7 \sim 11.7 GHz$	6.0	7.0	_	dB
7add	Power added efficiency			26		%
Rth(ch-c)	Thermal resistance * 1	△V _f method	_	-	3.5	°C/W

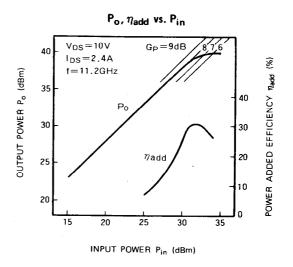
^{*1:} Channel to case

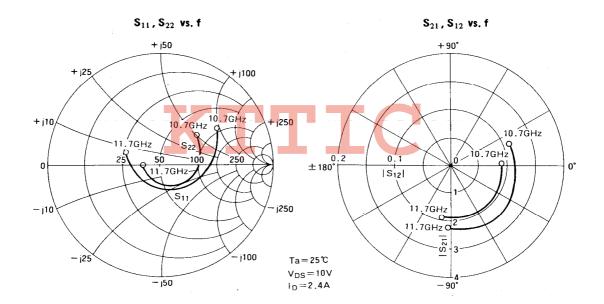


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TYPICAL CHARACTERISTICS (Ta = 25°C)







SPARAMETERS ($T_a=25^{\circ}C$, $V_{DS}=10V$, $I_{DS}=2.4A$)

f (GHz) -	S Parameters (TYP.)							
	S ₁₁		S ₂₁		S ₁₂		S ₂₂	
	Magn,	Angle (deg.)	Magn.	Angle (deg.)	Magn.	Angle (deg.)	Magn.	Angle (deg.)
10.7	0.64	40	2.15	23	0.082	2	0.44	41
10.9	0.50	15	2.28	-4	0.085	- 14	0.34	14
11.1	0.34	- 15	2.38	- 25	0.087	-34	0.24	- 17
11.3	0.16	-71	2.45	- 52	0.093	-57	0.14	- 73
11.5	0.20	- 168	2.30	-73	0.092	-79	0.16	— 136
11.7	0.32	151	2.15	-93	0.087	-98	0.18	176

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MITSUBISHI SEMICONDUCTOR < GaAs FET>

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